Dual General Purpose Transistor

PNP Dual

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-563 which is designed for low power surface mount applications.

Features

- Lead–Free Solder Plating
- Low $V_{CE(SAT)}$, < 0.5 V
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-60	V
Collector - Base Voltage	V _{CBO}	-50	V
Emitter-Base Voltage	V _{EBO}	-6.0	V
Collector Current – Continuous	I _C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P _D	357 (Note 1) 2.9 (Note 1)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	350 (Note 1)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	P _D	500 (Note 1) 4.0 (Note 1)	mW mW/°C
Thermal Resistance,	$R_{\theta JA}$	250	°C/W
Junction-to-Ambient	0071	(Note 1)	

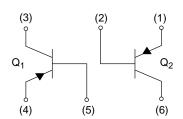
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 @ Minimum Pad.



ON Semiconductor®

http://onsemi.com





SOT-563 CASE 463A STYLE 1

MARKING DIAGRAM



3T = Specific Device Code

M = Month Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector–Base Breakdown Voltage (I _C = –50 μAdc, I _E = 0)	V _(BR) CBO	-60	-	-	Vdc
Collector–Emitter Breakdown Voltage $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V _{(BR)CEO}	-50	-	-	Vdc
Emitter–Base Breakdown Voltage (I _E = –50 μAdc, I _E = 0)	V _{(BR)EBO}	-6.0	-	-	Vdc
Collector–Base Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_E = 0)$	I _{CBO}	-	-	-0.5	nA
Emitter–Base Cutoff Current (V _{EB} = -5.0 Vdc, I _B = 0)	I _{EBO}	-	-	-0.5	μА
Collector–Emitter Saturation Voltage (Note 2) (I _C = -50 mAdc, I _B = -5.0 mAdc)	V _{CE(sat)}	-	-	-0.5	Vdc
DC Current Gain (Note 2) $(V_{CE} = -6.0 \text{ Vdc}, I_C = -1.0 \text{ mAdc})$	h _{FE}	120	_	560	_
Transition Frequency $(V_{CE} = -12 \text{ Vdc}, I_{C} = -2.0 \text{ mAdc}, f = 30 \text{ MHz})$	f _T	-	140	_	MHz
Output Capacitance $(V_{CB} = -12 \text{ Vdc}, I_E = 0 \text{ Adc}, f = 1 \text{ MHz})$	C _{OB}	-	3.5	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width \leq 300 μ s, D.C. \leq 2%.

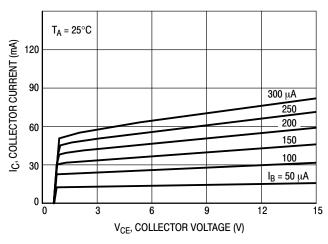
ORDERING INFORMATION

Device	Package	Shipping [†]
EMT1DXV6T1G	SOT-563 (Pb-Free)	4000 / Tape & Reel
NSVEMT1DXV6T1G*	SOT-563 (Pb-Free)	4000 / Tape & Reel
EMT1DXV6T5G	SOT-563 (Pb-Free)	8000 / Tape & Reel
NSVEMT1DXV6T5G*	SOT-563 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP

Capable.

TYPICAL CHARACTERISTICS



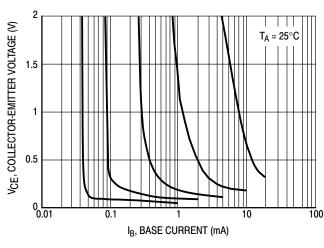
1000

T_A = 75°C

T_A = 25°C

Figure 1. I_C – V_{CE}

Figure 2. DC Current Gain



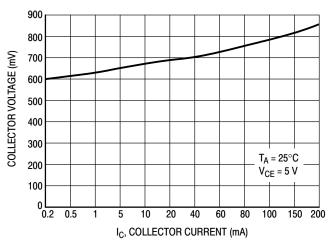
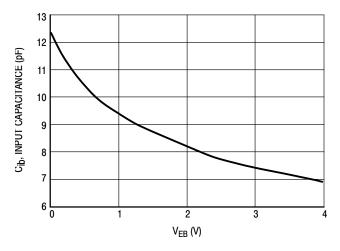


Figure 3. Collector Saturation Region

Figure 4. On Voltage



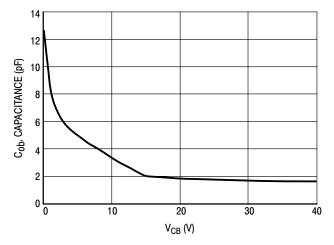
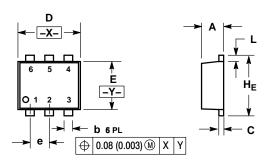


Figure 5. Capacitance

Figure 6. Capacitance

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A ISSUE F



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
 FINISH THICKNESS. MINIMUM LEAD THICKNESS
 IS THE MINIMUM THICKNESS OF BASE MATERIAL.

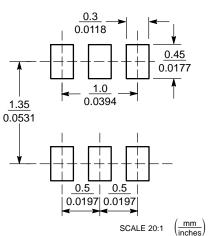
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
Е	1.10	1.20	1.30	0.043	0.047	0.051
е	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

STYLE 1: PIN 1. EMITTER 1

2. BASE 13. COLLECTOR 24. EMITTER 2

BASE 2 COLLECTOR 1

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent—Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA **Phone**: 303–675–2175 or 800–344–3860 Toll Free USA/Canada

Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

EMT1DXV6T1G EMT1DXV6T5G